

IRFI4510GPbF

HEXFET® Power MOSFET

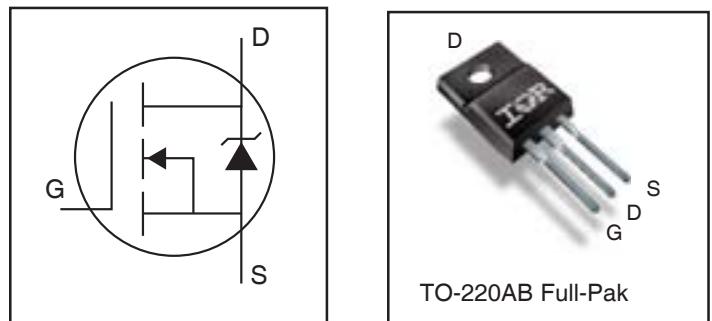
Applications

- High Efficiency Synchronous Rectification in SMPS
- Uninterruptible Power Supply
- High Speed Power Switching
- Hard Switched and High Frequency Circuits

V_{DSS}	100V
R_{D(on)} typ.	10.7mΩ
	max. 13.5mΩ
I_D	35A

Benefits

- Improved Gate, Avalanche and Dynamic dV/dt Ruggedness
- Fully Characterized Capacitance and Avalanche SOA
- Enhanced body diode dV/dt and di/dt Capability
- Lead-Free
- Halogen-Free



G	D	S
Gate	Drain	Source

Absolute Maximum Ratings

Symbol	Parameter	Max.	Units
I _D @ T _C = 25°C	Continuous Drain Current, V _{GS} @ 10V	35	A
I _D @ T _C = 100°C	Continuous Drain Current, V _{GS} @ 10V	24	
I _{DM}	Pulsed Drain Current ①	180	
P _D @ T _C = 25°C	Maximum Power Dissipation	42	W
	Linear Derating Factor	0.28	W/°C
V _{GS}	Gate-to-Source Voltage	±20	V
E _{AS} (Thermally limited)	Single Pulse Avalanche Energy ②	206	mJ
T _J	Operating Junction and	-55 to + 175	°C
T _{STG}	Storage Temperature Range		
	Soldering Temperature, for 10 seconds (1.6mm from case)	300	
	Mounting torque, 6-32 or M3 screw	10lb·in (1.1N·m)	

Thermal Resistance

	Parameter	Typ.	Max.	Units
R _{θJC}	Junction-to-Case ④	—	3.6	°C/W
R _{θJA}	Junction-to-Ambient ④	—	65	

Static @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(\text{BR})\text{DSS}}$	Drain-to-Source Breakdown Voltage	100	—	—	V	$V_{GS} = 0V, I_D = 250\mu\text{A}$
$\Delta V_{(\text{BR})\text{DSS}}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.11	—	V/ $^\circ\text{C}$	Reference to $25^\circ\text{C}, I_D = 5\text{mA}$ ③
$R_{DS(\text{on})}$	Static Drain-to-Source On-Resistance	—	10.7	13.5	$\text{m}\Omega$	$V_{GS} = 10V, I_D = 21\text{A}$ ④
$V_{GS(\text{th})}$	Gate Threshold Voltage	2.0	—	4.0	V	$V_{DS} = V_{GS}, I_D = 100\mu\text{A}$
I_{DSS}	Drain-to-Source Leakage Current	—	—	20	μA	$V_{DS} = 100V, V_{GS} = 0V$
		—	—	250	μA	$V_{DS} = 100V, V_{GS} = 0V, T_J = 125^\circ\text{C}$
I_{GS}	Gate-to-Source Forward Leakage	—	—	100	nA	$V_{GS} = 20V$
	Gate-to-Source Reverse Leakage	—	—	-100	nA	$V_{GS} = -20V$
$R_{G(\text{int})}$	Internal Gate Resistance	—	0.6	—	Ω	

Dynamic @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
g_{fs}	Forward Transconductance	55	—	—	S	$V_{DS} = 50V, I_D = 21\text{A}$
Q_g	Total Gate Charge	—	54	81	nC	$I_D = 21\text{A}$
Q_{gs}	Gate-to-Source Charge	—	13	—	nC	$V_{DS} = 50V$
Q_{gd}	Gate-to-Drain ("Miller") Charge	—	16	—	nC	$V_{GS} = 10V$ ③
$t_{d(on)}$	Turn-On Delay Time	—	16	—	ns	$V_{DD} = 65V$
t_r	Rise Time	—	33	—	ns	$I_D = 21\text{A}$
$t_{d(off)}$	Turn-Off Delay Time	—	54	—	ns	$R_G = 7.5\Omega$
t_f	Fall Time	—	37	—	ns	$V_{GS} = 10V$ ③
C_{iss}	Input Capacitance	—	2998	—	pF	$V_{GS} = 0V$
C_{oss}	Output Capacitance	—	216	—	pF	$V_{DS} = 50V$
C_{rss}	Reverse Transfer Capacitance	—	103	—	pF	$f = 1.0\text{MHz}$
$C_{oss \text{ eff. (ER)}}$	Effective Output Capacitance (Energy Related)	—	261	—		$V_{GS} = 0V, V_{DS} = 0V \text{ to } 80V$ ⑤, See Fig.11
$C_{oss \text{ eff. (TR)}}$	Effective Output Capacitance (Time Related)	—	494	—		$V_{GS} = 0V, V_{DS} = 0V \text{ to } 80V$ ⑤

Diode Characteristics

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	35	A	MOSFET symbol showing the integral reverse p-n junction diode.
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	180	A	
V_{SD}	Diode Forward Voltage	—	—	1.3	V	$T_J = 25^\circ\text{C}, I_S = 21\text{A}, V_{GS} = 0V$ ③
t_{rr}	Reverse Recovery Time	—	39	59	ns	$T_J = 25^\circ\text{C}$ $V_R = 85V$
		—	47	71	ns	$T_J = 125^\circ\text{C}$ $I_F = 21\text{A}$
Q_{rr}	Reverse Recovery Charge	—	63	95	nC	$T_J = 25^\circ\text{C}$ $dI/dt = 100\text{A}/\mu\text{s}$ ③
		—	90	135	nC	$T_J = 125^\circ\text{C}$
I_{RRM}	Reverse Recovery Current	—	2.9	—	A	$T_J = 25^\circ\text{C}$
t_{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Limited by $T_{J\text{max}}$, starting $T_J = 25^\circ\text{C}$, $L = 0.93\text{mH}$
 $R_G = 50\Omega$, $I_{AS} = 21\text{A}$, $V_{GS} = 10V$. Part not recommended for use above this value.
- ③ Pulse width $\leq 400\mu\text{s}$; duty cycle $\leq 2\%$.
- ④ R_0 is measured at T_J approximately 90°C .

⑤ $C_{oss \text{ eff. (TR)}}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS} .

⑥ $C_{oss \text{ eff. (ER)}}$ is a fixed capacitance that gives the same energy as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS} .

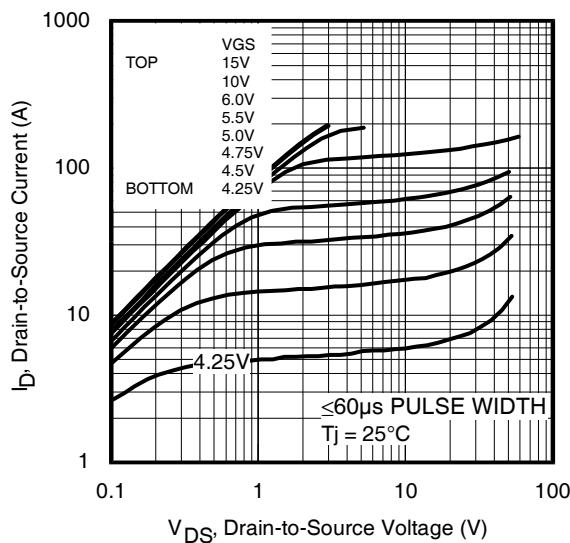


Fig 1. Typical Output Characteristics

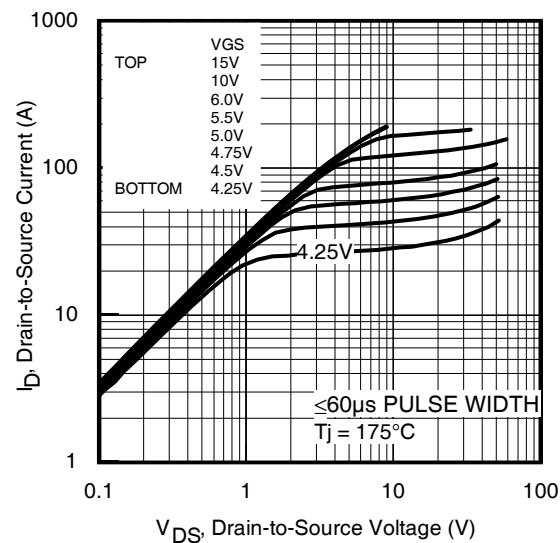


Fig 2. Typical Output Characteristics

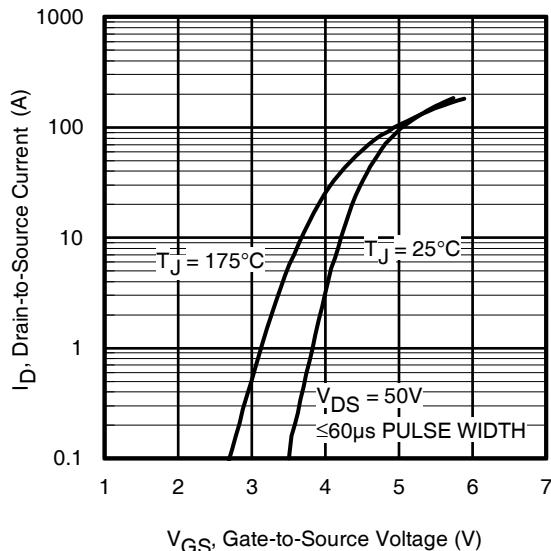


Fig 3. Typical Transfer Characteristics

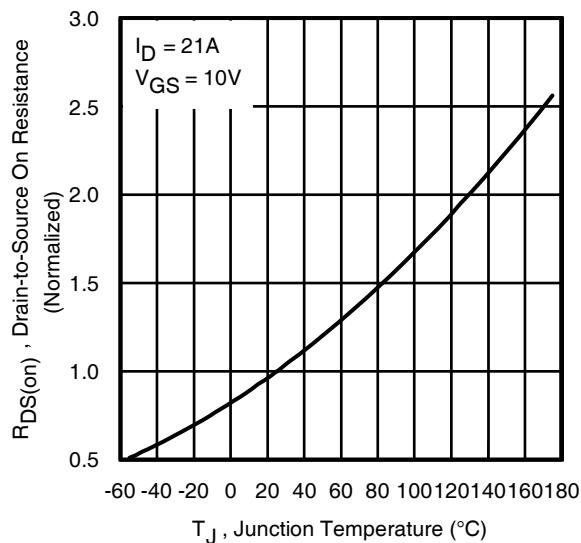


Fig 4. Normalized On-Resistance vs. Temperature

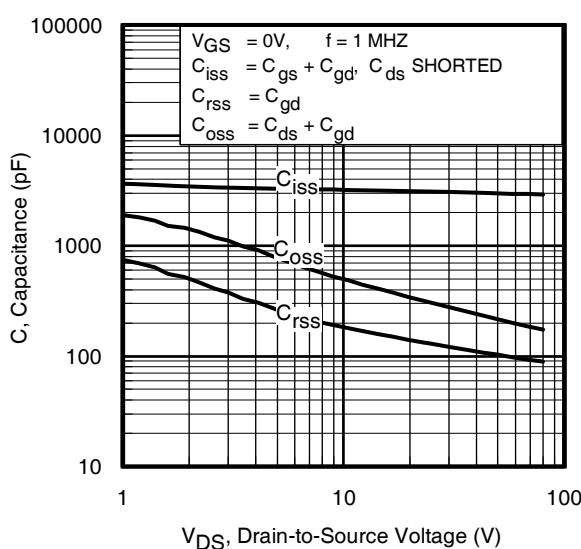


Fig 5. Typical Capacitance vs. Drain-to-Source Voltage

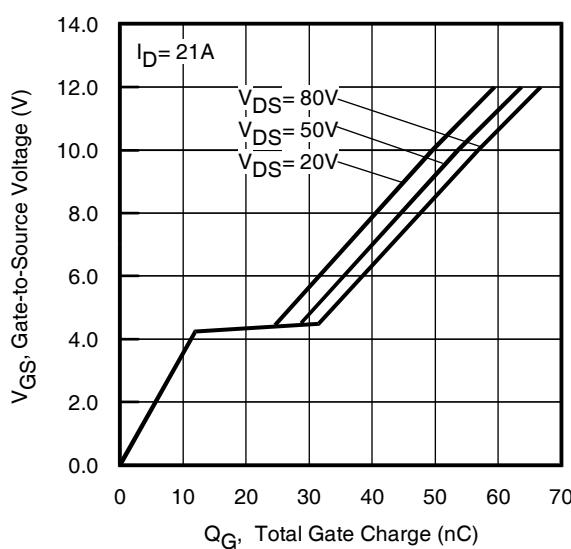


Fig 6. Typical Gate Charge vs. Gate-to-Source Voltage

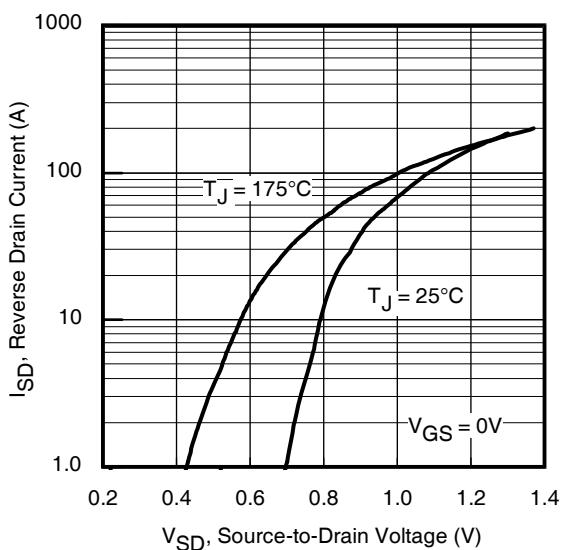


Fig 7. Typical Source-Drain Diode Forward Voltage

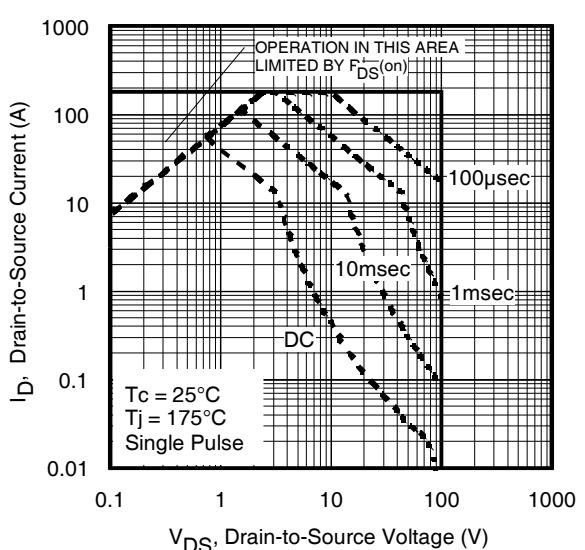


Fig 8. Maximum Safe Operating Area

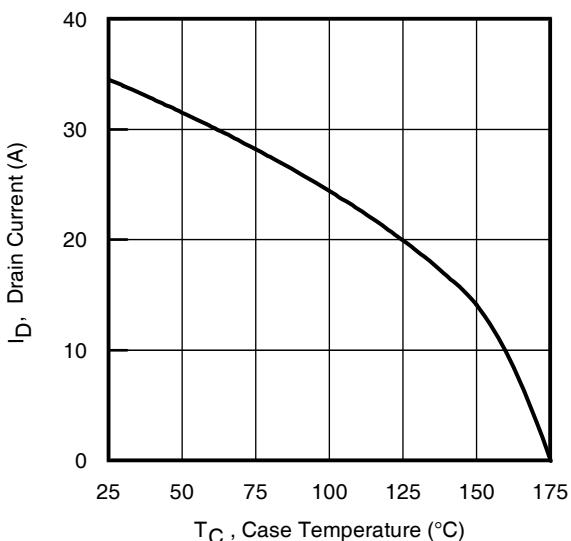


Fig 9. Maximum Drain Current vs. Case Temperature

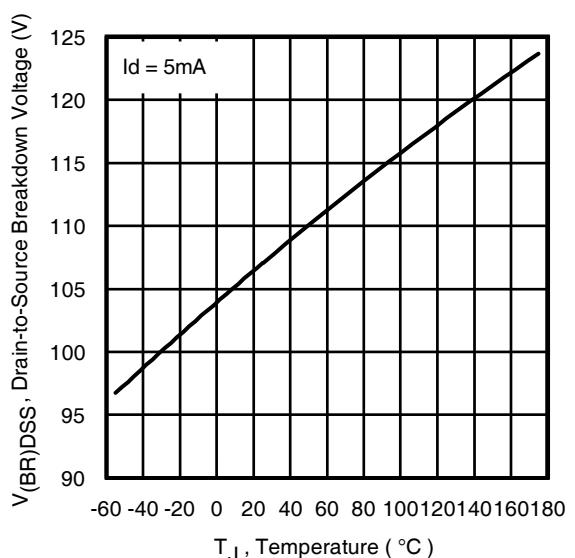


Fig 10. Drain-to-Source Breakdown Voltage

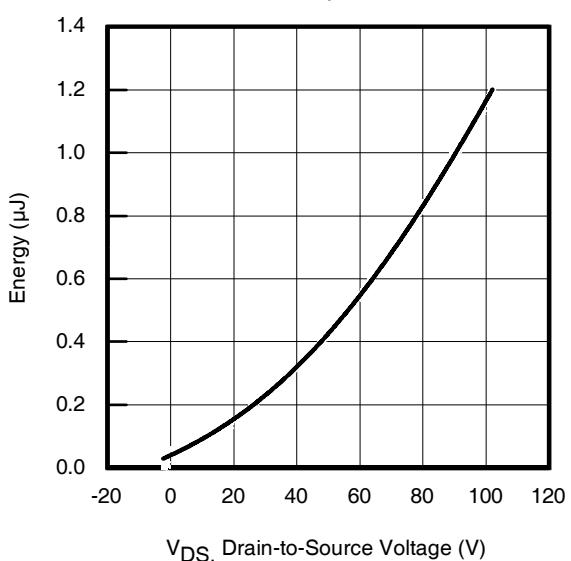


Fig 11. Typical C_{oss} Stored Energy

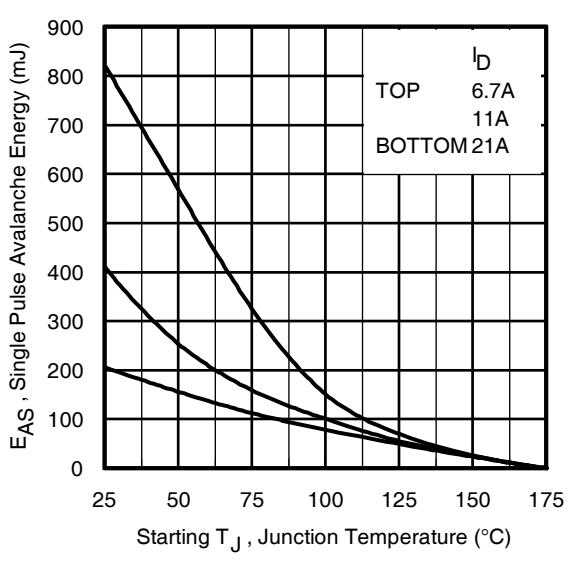


Fig 12. Maximum Avalanche Energy vs. DrainCurrent

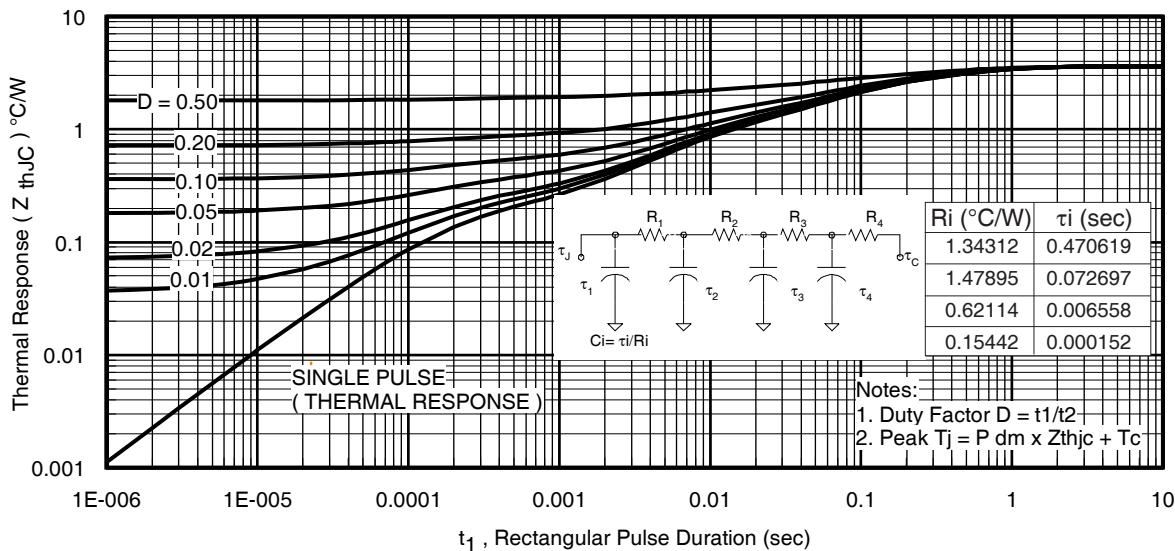


Fig 13. Maximum Effective Transient Thermal Impedance, Junction-to-Case

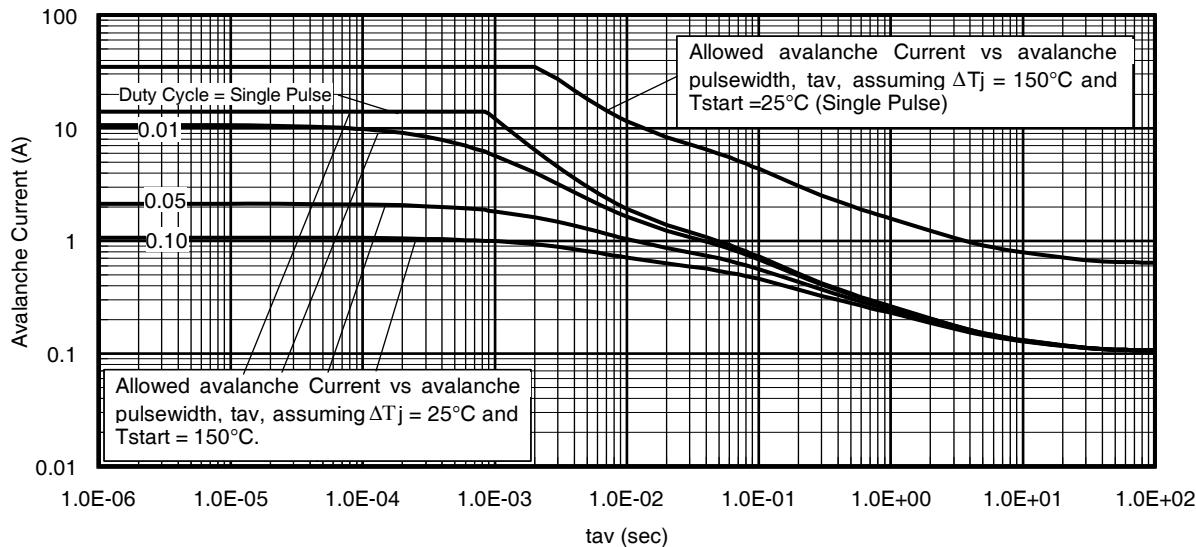


Fig 14. Typical Avalanche Current vs.Pulsewidth

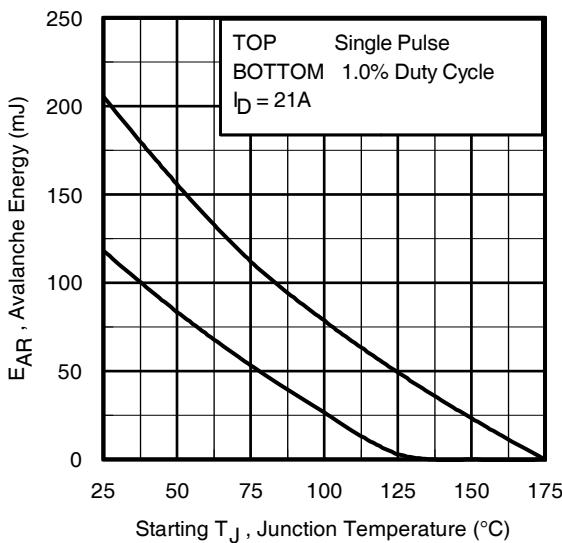
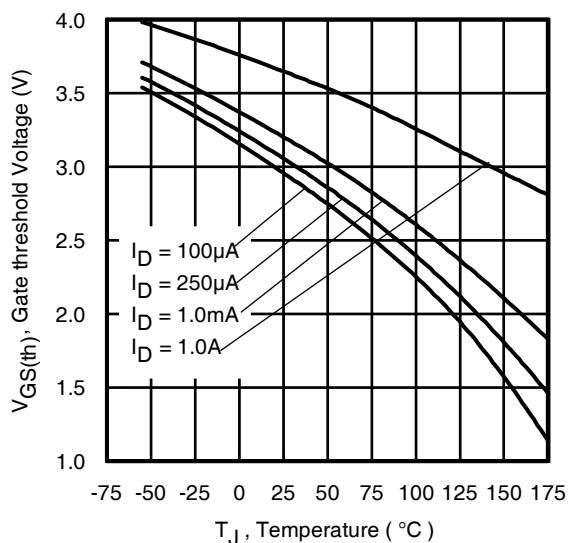
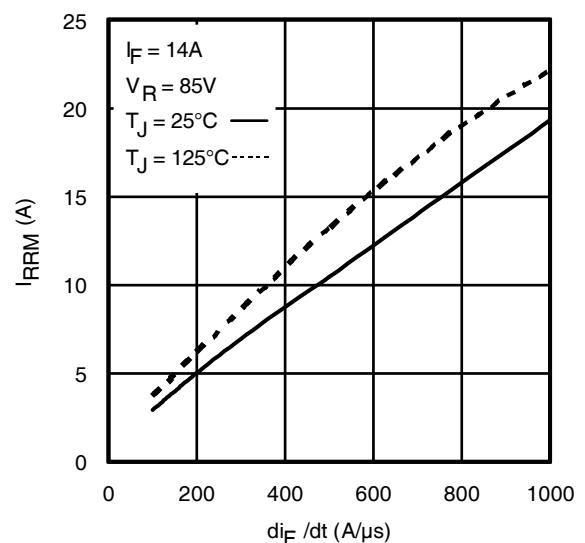
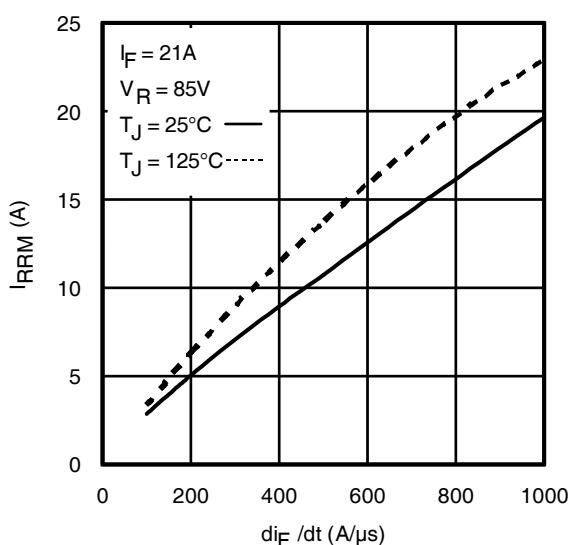
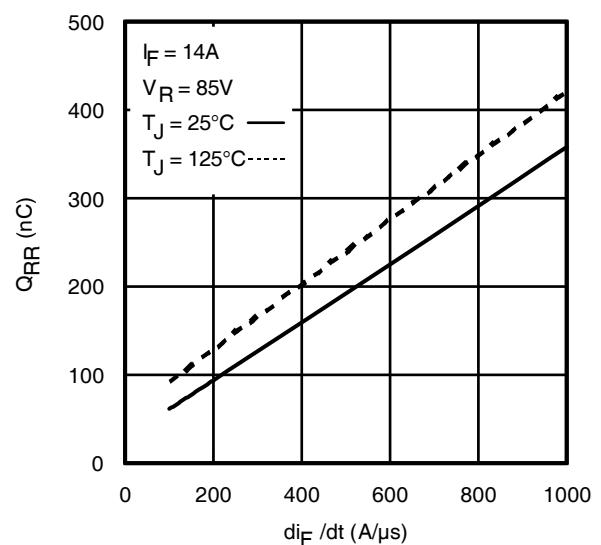
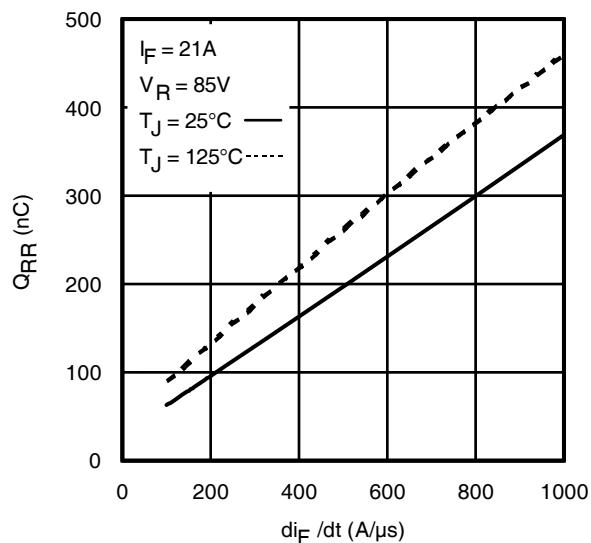


Fig 15. Maximum Avalanche Energy vs. Temperature

Notes on Repetitive Avalanche Curves , Figures 14, 15:
 (For further info, see AN-1005 at www.irf.com)

1. Avalanche failures assumption:
 Purely a thermal phenomenon and failure occurs at a temperature far in excess of T_{jmax} . This is validated for every part type.
2. Safe operation in Avalanche is allowed as long as T_{jmax} is not exceeded.
3. Equation below based on circuit and waveforms shown in Figures 22a, 22b.
4. $P_{D(ave)}$ = Average power dissipation per single avalanche pulse.
5. BV = Rated breakdown voltage (1.3 factor accounts for voltage increase during avalanche).
6. I_{av} = Allowable avalanche current.
7. ΔT = Allowable rise in junction temperature, not to exceed T_{jmax} (assumed as 25°C in Figure 14, 15).
- t_{av} = Average time in avalanche.
- D = Duty cycle in avalanche = $t_{av} \cdot f$
- $Z_{thJC}(D, t_{av})$ = Transient thermal resistance, see Figures 13

$$\begin{aligned} P_{D(ave)} &= 1/2 (1.3 \cdot BV \cdot I_{av}) = \Delta T / Z_{thJC} \\ I_{av} &= 2\Delta T / [1.3 \cdot BV \cdot Z_{th}] \\ E_{AS(AR)} &= P_{D(ave)} \cdot t_{av} \end{aligned}$$

**Fig. 16.** Threshold Voltage vs. Temperature**Fig. 17 -** Typical Recovery Current vs. di_f/dt **Fig. 18 -** Typical Recovery Current vs. di_f/dt **Fig. 19 -** Typical Stored Charge vs. di_f/dt **Fig. 20 -** Typical Stored Charge vs. di_f/dt

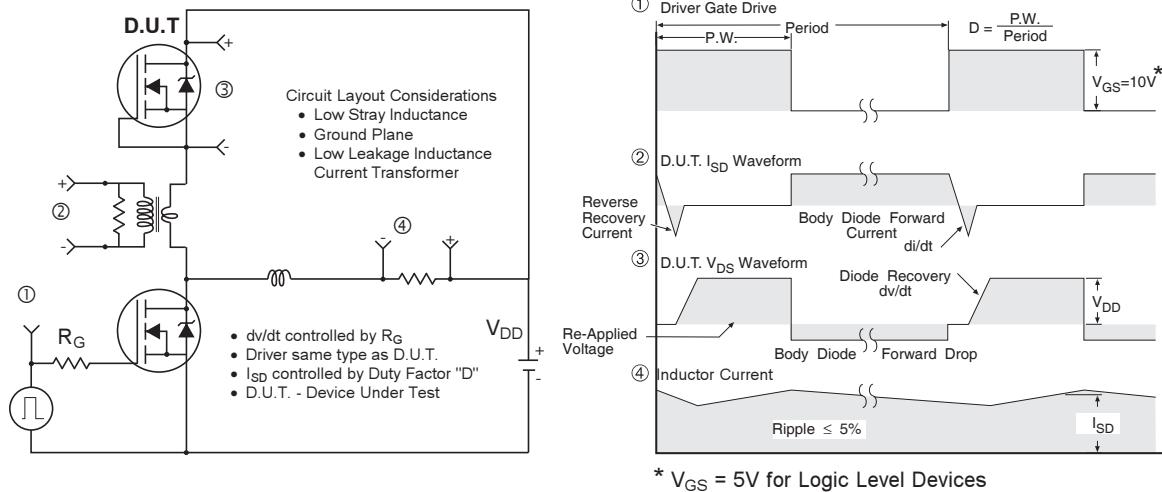


Fig 21. Peak Diode Recovery dv/dt Test Circuit for N-Channel HEXFET® Power MOSFETs

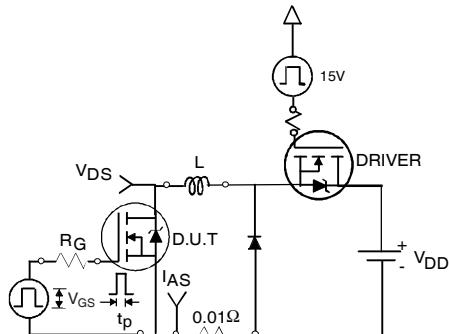


Fig 22a. Unclamped Inductive Test Circuit

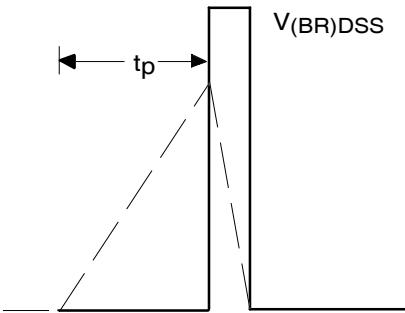


Fig 22b. Unclamped Inductive Waveforms

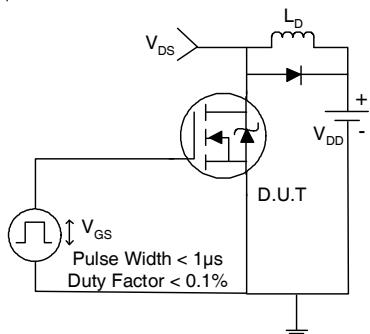


Fig 23a. Switching Time Test Circuit

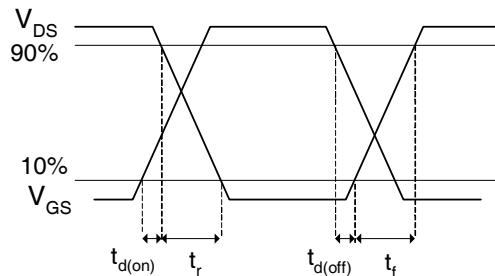


Fig 23b. Switching Time Waveforms

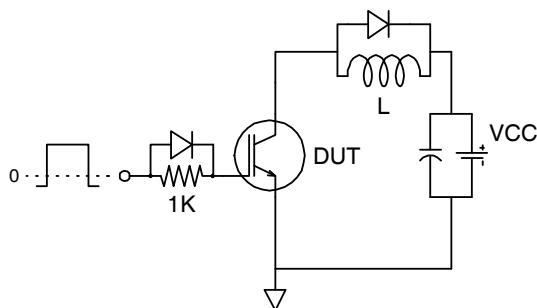


Fig 24a. Gate Charge Test Circuit
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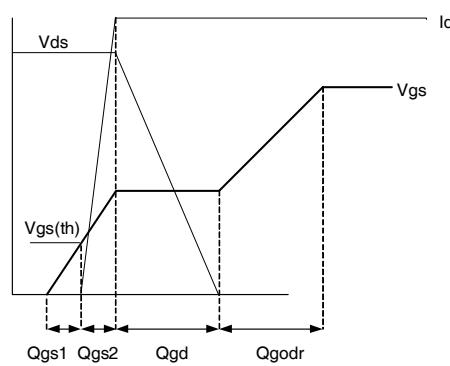
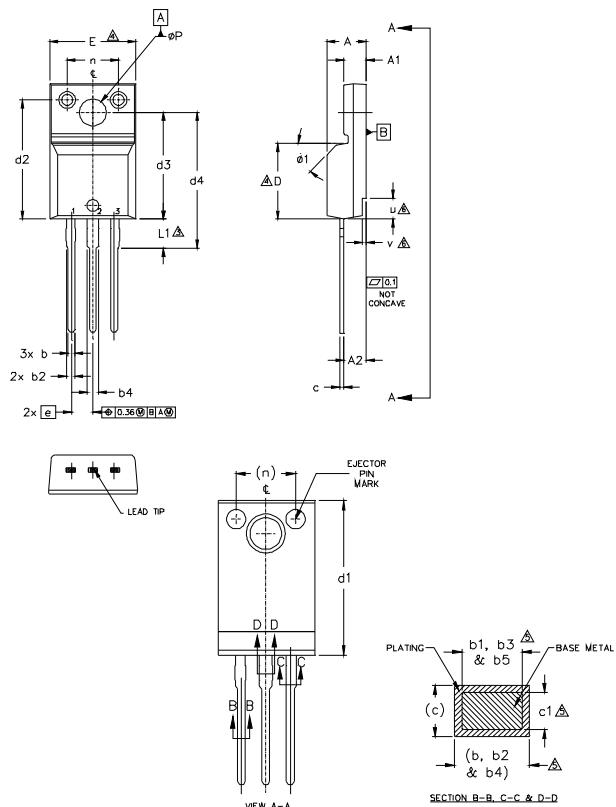


Fig 24b. Gate Charge Waveform

TO-220AB Full-Pak Package Outline (Dimensions are shown in millimeters (inches))



NOTES:

- 1.0 DIMENSIONING AND TOLERANCING AS PER ASME Y14.5 M- 1994.
- 2.0 DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
- 3.0 LEAD DIMENSION AND FINISH UNCONTROLLED IN L1.
- 4.0 DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .005" (0.127) PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTER MOST EXTREMES OF THE PLASTIC BODY.
- 5.0 DIMENSION b1, b3, b5 & c1 APPLY TO BASE METAL ONLY.
- 6.0 STEP OPTIONAL ON PLASTIC BODY DEFINED BY DIMENSIONS u & v.
- 7.0 CONTROLLING DIMENSION : INCHES.

SYMBOL	DIMENSIONS				NOTES	
	MILLIMETERS		INCHES			
	MIN.	MAX.	MIN.	MAX.		
A	4.57	4.83	.180	.190		
A1	2.57	2.83	.101	.111		
A2	2.41	2.92	.095	.115		
b	0.62	.094	.024	.037		
b1	0.62	0.89	.024	.035	5	
b2	0.76	1.27	.030	.050		
b3	0.76	1.22	.030	.048	5	
b4	1.02	1.52	.040	.060		
b5	1.02	1.47	.040	.058	5	
c	0.33	0.63	.013	.025		
c1	0.33	0.58	.013	.023	5	
D	8.65	9.80	.341	.386	4	
d1	15.80	16.12	.622	.635		
d2	13.97	14.22	.550	.560		
d3	12.30	12.92	.484	.509		
d4	8.64	9.91	.340	.390		
E	9.63	10.63	.379	.419	4	
e	2.54	BSC	.100 BSC			
L	13.20	13.72	.520	.540		
L1	3.10	2.31	.122	.138	3	
n	6.05	6.15	.238	.242		
φP	3.05	3.45	.120	.136		
u	2.40	2.50	.094	.098	6	
v	0.40	0.50	.016	.020	6	
φ1	—	45°	—	45°		

LEAD ASSIGNMENTS

HEXFET

- 1.- GATE
- 2.- DRAIN
- 3.- SOURCE

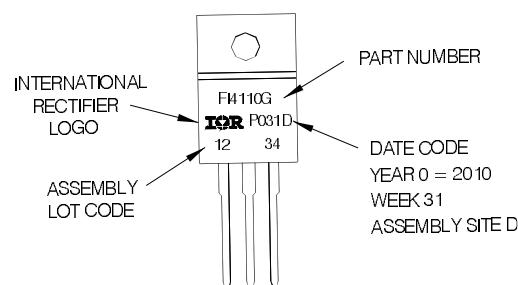
IGBTs_CoPACK

- 1.- GATE
- 2.- COLLECTOR
- 3.- Emitter

TO-220AB Full-Pak Part Marking Information

EXAMPLE: THIS IS AN IRFI4110G
WITH ASSEMBLY
LOT CODE 1234
ASSEMBLED ON WW 31, 2010

Notes: - "P" in assembly line position indicates "Lead-Free"
- "G" suffix in part number indicates "Halogen-Free"



TO-220AB Full-Pak packages are not recommended for Surface Mount Application.

Note: For the most current drawing please refer to IR website at: <http://www.irf.com/package/>

Data and specifications subject to change without notice.
This product has been designed and qualified for the Industrial market.
Qualification Standards can be found on IR's Web site.

International
IR Rectifier

IR WORLD HEADQUARTERS: 101N Sepulveda Blvd, El Segundo, California 90245, USA Tel: (310) 252-7105
TAC Fax: (310) 252-7903

Visit us at www.irf.com for sales contact information. 05/2012

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